Discrete POWER & Signal **Technologies** 

# 1N4150 / FDLL4150



DO-35

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LL-34 THE PLACEMENT OF THE EXPANSION GAP HAS NO RELATIONSHIP TO THE LOCATION OF THE CATHODE TERMINAL

COLOR BAND MARKING DEVICE 1ST BAND 2ND BAND FDLL4150 BLACK ORANGE

## **High Conductance Ultra Fast Diode**

Sourced from Process 1R. See MMBD1201-1205 for characteristics.

#### Absolute Maximum Ratings\* TA = 25°C unless otherwise noted

| Symbol                             | Parameter   | Value       | Units  |
|------------------------------------|---|-------------|--------|
| W <sub>IV</sub>                    | Working Inverse Voltage   | 50          | V      |
| lo                                 | Average Rectified Current   | 200         | mA     |
| I <sub>F</sub>                     | DC Forward Current  | 400         | mA     |
| İf                                 | Recurrent Peak Forward Current  | 600         | mA     |
| İ <sub>f(surge)</sub>              | Peak Forward Surge Current<br>Pulse width = 1.0 second<br>Pulse width = 1.0 microsecond | 1.0<br>4.0  | A<br>A |
| T <sub>stg</sub><br>T <sub>J</sub> | Storage Temperature Range   | -65 to +200 | °C     |
| TJ                                 | Operating Junction Temperature  | 175         | °C     |

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES: 1) These ratings are based on a maximum junction temperature of 200 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### **Thermal Characteristics** TA = 25°C unless otherwise noted

| Symbol                | Characteristic                          | Мах            | Units |
|-----------------------|---|----------------|-------|
|                       |   | 1N / FDLL 4150 |       |
| PD                    | Total Device Dissipation                | 500            | mW    |
|                       | Derate above 25°C                       | 3.33           | mW/°C |
| $R_{	extsf{	heta}JA}$ | Thermal Resistance, Junction to Ambient | 300            | °C/W  |

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# High Conductance Ultra Fast Diode (continued)

### **Electrical Characteristics**

TA = 25°C unless otherwise noted

| Symbol          | Parameter             | Test Conditions  | Min                              | Max                             | Units                     |
|-----------------|-----------------------|--|----------------------------------|---------------------------------|---------------------------|
| B <sub>V</sub>  | Breakdown Voltage     | I <sub>R</sub> = 5.0 μA  | 75                               |                                 | V                         |
| I <sub>R</sub>  | Reverse Current       | V <sub>R</sub> = 50 V<br>V <sub>R</sub> = 50 V, T <sub>A</sub> = 150°C   |                                  | 100<br>100                      | nA<br>μA                  |
| V <sub>F</sub>  | Forward Voltage       | $I_F = 1.0 \text{ mA}$<br>$I_F = 10 \text{ mA}$<br>$I_F = 50 \text{ mA}$<br>$I_F = 100 \text{ mA}$<br>$I_F = 200 \text{ mA}$ | 540<br>660<br>760<br>820<br>0.87 | 620<br>740<br>860<br>920<br>1.0 | mV<br>mV<br>mV<br>mV<br>V |
| Co              | Diode Capacitance     | V <sub>R</sub> = 0, f = 1.0 MHz  |                                  | 2.5                             | pF                        |
| T <sub>RR</sub> | Reverse Recovery Time | $I_F = I_R = 10 \text{ mA-}200 \text{ mA}, R_L = 100\Omega$<br>$I_F = I_R = 200 \text{ mA-}400 \text{ mA}, R_L = 100\Omega$  |                                  | 4.0<br>6.0                      | nS<br>nS                  |
| T <sub>FR</sub> | Forward Recovery Time | $I_F = 200 \text{ mA}, V_{FR} = 1.0 \text{ V}$   |                                  | 10                              | nS                        |

# 1N4150 / FDLL4150

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